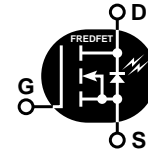
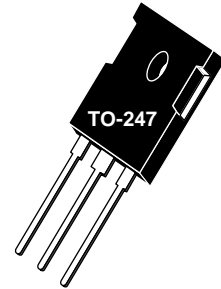


### POWER MOS V®

**FREDFET**

Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



- Fast Recovery Body Diode
- Lower Leakage
- Faster Switching
- 100% Avalanche Tested
- Popular TO-247 Package

#### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

| Symbol         | Parameter  | APT8065BVFR | UNIT  |
|----------------|--|-------------|-------|
| $V_{DSS}$      | Drain-Source Voltage   | 800         | Volts |
| $I_D$          | Continuous Drain Current @ $T_C = 25^\circ\text{C}$            | 13          | Amps  |
| $I_{DM}$       | Pulsed Drain Current <sup>①</sup>                              | 52          |       |
| $V_{GS}$       | Gate-Source Voltage Continuous                                 | $\pm 30$    | Volts |
| $V_{GSM}$      | Gate-Source Voltage Transient                                  | $\pm 40$    |       |
| $P_D$          | Total Power Dissipation @ $T_C = 25^\circ\text{C}$             | 280         | Watts |
|                | Linear Derating Factor   | 2.24        | W/°C  |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range               | -55 to 150  | °C    |
| $T_L$          | Lead Temperature: 0.063" from Case for 10 Sec.                 | 300         |       |
| $I_{AR}$       | Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive) | 13          | Amps  |
| $E_{AR}$       | Repetitive Avalanche Energy <sup>①</sup>                       | 30          | mJ    |
| $E_{AS}$       | Single Pulse Avalanche Energy <sup>④</sup>                     | 1210        |       |

#### STATIC ELECTRICAL CHARACTERISTICS

| Symbol       | Characteristic / Test Conditions   | MIN | TYP | MAX       | UNIT          |
|--------------|--|-----|-----|-----------|---------------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )                             | 800 |     |           | Volts         |
| $I_{D(on)}$  | On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ ) | 13  |     |           | Amps          |
| $R_{DS(on)}$ | Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, 0.5 I_{D[Cont.]}$ )                 |     |     | 0.65      | Ohms          |
| $I_{DSS}$    | Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}, V_{GS} = 0V$ )                                |     |     | 250       | $\mu\text{A}$ |
|              | Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )   |     |     | 1000      |               |
| $I_{GSS}$    | Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )                                    |     |     | $\pm 100$ | nA            |
| $V_{GS(th)}$ | Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 1.0\text{mA}$ )                                   | 2   |     | 4         | Volts         |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

**DYNAMIC CHARACTERISTICS**

**APT8065BVFR**

| Symbol              | Characteristic                 | Test Conditions                                | MIN | TYP  | MAX  | UNIT |
|---------------------|--------------------------------|--|-----|------|------|------|
| C <sub>iss</sub>    | Input Capacitance              | V <sub>GS</sub> = 0V                           |     | 3050 | 3700 | pF   |
| C <sub>oss</sub>    | Output Capacitance             | V <sub>DS</sub> = 25V                          |     | 300  | 420  |      |
| C <sub>rss</sub>    | Reverse Transfer Capacitance   | f = 1 MHz                                      |     | 150  | 225  |      |
| Q <sub>g</sub>      | Total Gate Charge <sup>③</sup> | V <sub>GS</sub> = 10V                          |     | 150  | 225  | nC   |
| Q <sub>gs</sub>     | Gate-Source Charge             | V <sub>DD</sub> = 0.5 V <sub>DSS</sub>         |     | 17   | 25   |      |
| Q <sub>gd</sub>     | Gate-Drain ("Miller") Charge   | I <sub>D</sub> = I <sub>D</sub> [Cont.] @ 25°C |     | 70   | 105  |      |
| t <sub>d(on)</sub>  | Turn-on Delay Time             | V <sub>GS</sub> = 15V                          |     | 12   | 24   | ns   |
| t <sub>r</sub>      | Rise Time                      | V <sub>DD</sub> = 0.5 V <sub>DSS</sub>         |     | 11   | 22   |      |
| t <sub>d(off)</sub> | Turn-off Delay Time            | I <sub>D</sub> = I <sub>D</sub> [Cont.] @ 25°C |     | 60   | 90   |      |
| t <sub>f</sub>      | Fall Time                      | R <sub>G</sub> = 1.6Ω                          |     | 12   | 24   |      |

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

| Symbol           | Characteristic / Test Conditions  | MIN                    | TYP | MAX | UNIT  |
|------------------|---|------------------------|-----|-----|-------|
| I <sub>S</sub>   | Continuous Source Current (Body Diode)  |                        |     | 13  | Amps  |
| I <sub>SM</sub>  | Pulsed Source Current <sup>①</sup> (Body Diode)   |                        |     | 52  |       |
| V <sub>SD</sub>  | Diode Forward Voltage <sup>②</sup> (V <sub>GS</sub> = 0V, I <sub>S</sub> = -I <sub>D</sub> [Cont.]) |                        |     | 1.3 | Volts |
| dv/dt            | Peak Diode Recovery dv/dt <sup>⑤</sup>  |                        |     | 18  | V/ns  |
| t <sub>rr</sub>  | Reverse Recovery Time<br>(I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)                | T <sub>j</sub> = 25°C  |     | 200 | ns    |
|                  |   | T <sub>j</sub> = 125°C |     | 350 |       |
| Q <sub>rr</sub>  | Reverse Recovery Charge<br>(I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)              | T <sub>j</sub> = 25°C  |     | 0.7 | μC    |
|                  |   | T <sub>j</sub> = 125°C |     | 1.8 |       |
| I <sub>RRM</sub> | Peak Recovery Current<br>(I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)                | T <sub>j</sub> = 25°C  |     | 11  | Amps  |
|                  |   | T <sub>j</sub> = 125°C |     | 17  |       |

**THERMAL CHARACTERISTICS**

| Symbol           | Characteristic      | MIN | TYP | MAX  | UNIT |
|------------------|---------------------|-----|-----|------|------|
| R <sub>θJC</sub> | Junction to Case    |     |     | 0.45 | °C/W |
| R <sub>θJA</sub> | Junction to Ambient |     |     | 40   |      |

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting T<sub>j</sub> = +25°C, L = 14.32mH, R<sub>G</sub> = 25Ω, Peak I<sub>L</sub> = 13A

⑤ I<sub>S</sub> = -I<sub>D</sub> [Cont.], di/dt = 100A/μs, V<sub>DD</sub> - V<sub>DSS</sub>, T<sub>j</sub> = 150°C, R<sub>G</sub> = 2.0Ω, V<sub>R</sub> = 200V.

APT Reserves the right to change, without notice, the specifications and information contained herein.

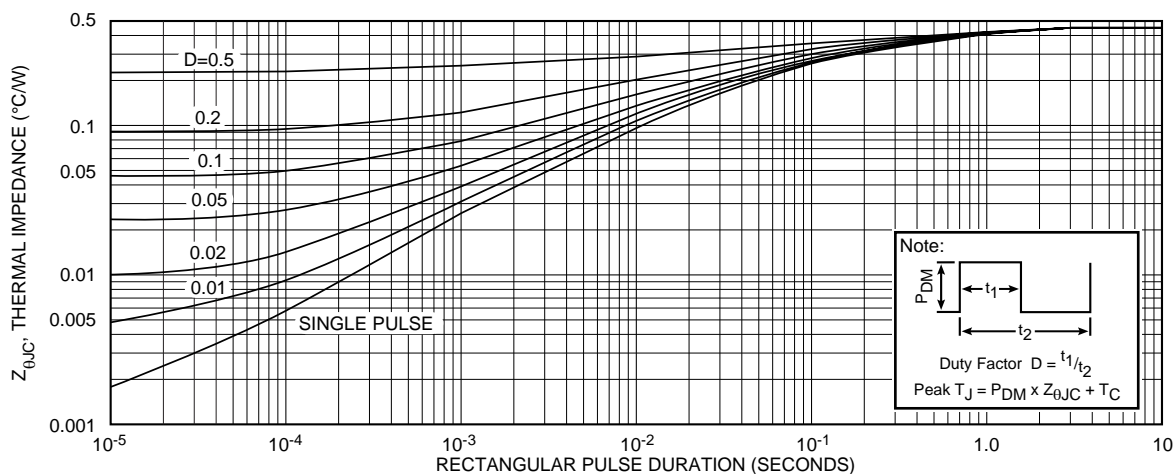
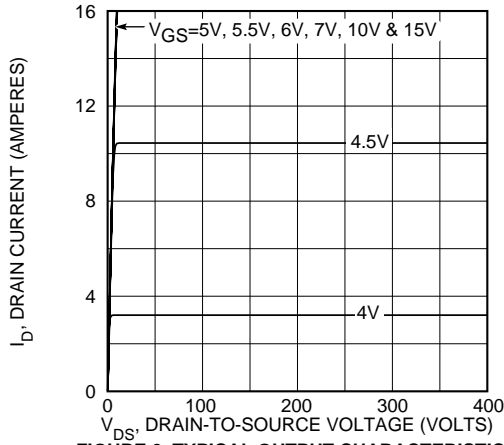
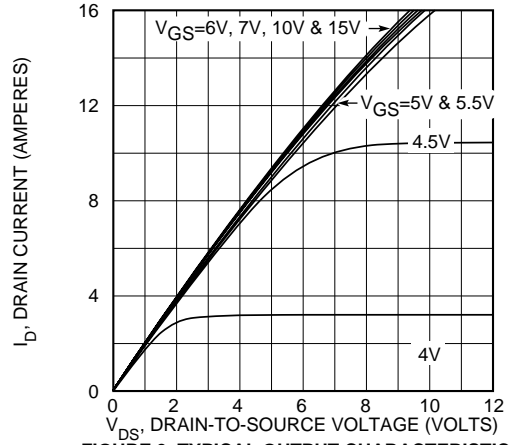


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

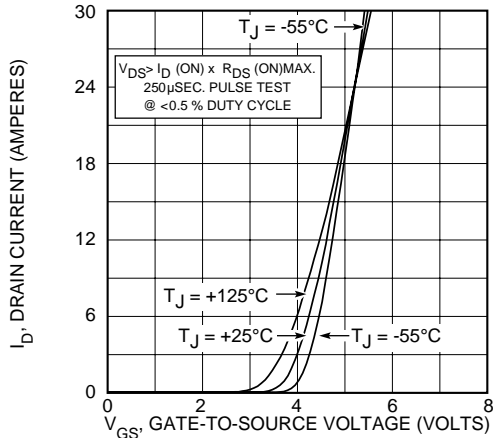
**APT8065BVFR**



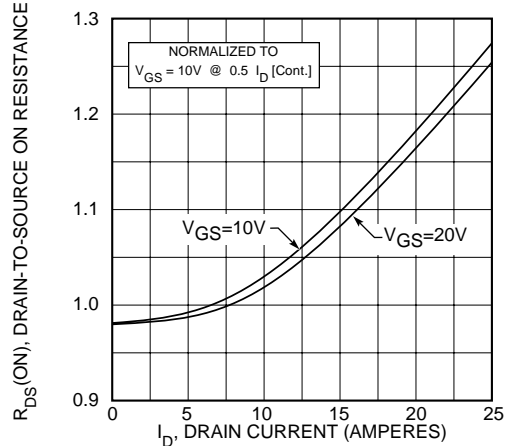
**FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS**



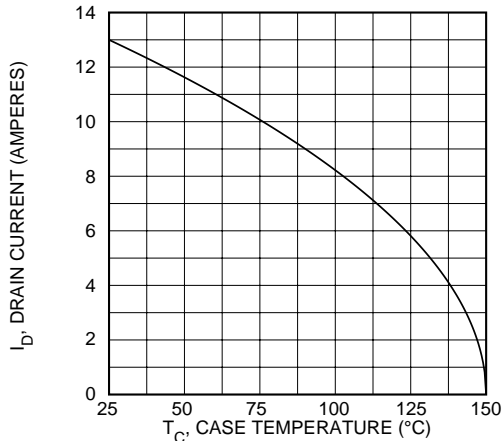
**FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS**



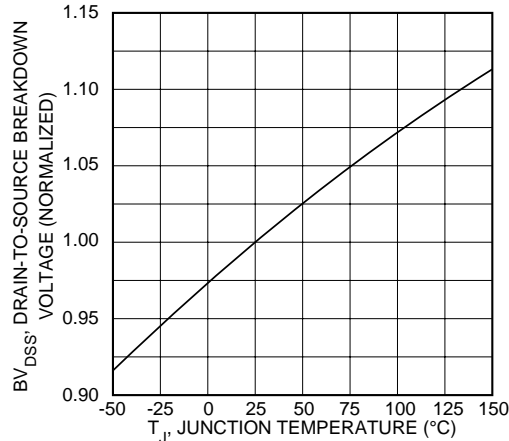
**FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS**



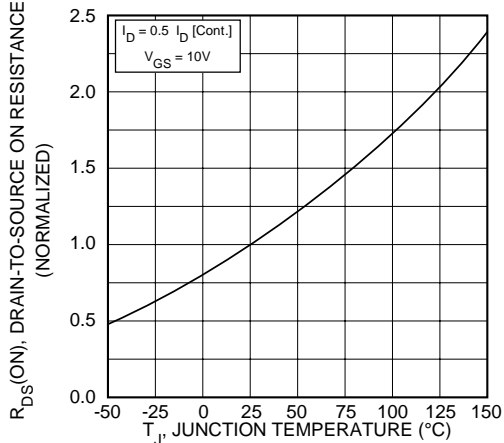
**FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT**



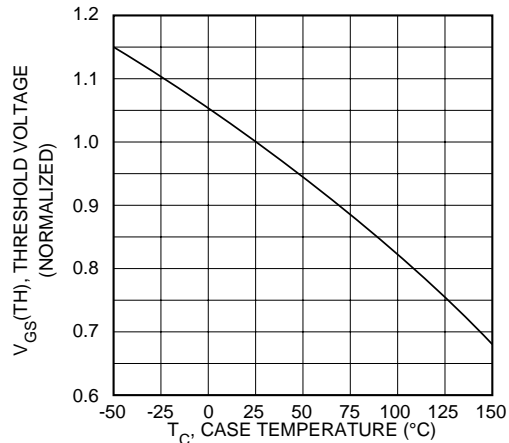
**FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE**



**FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE**

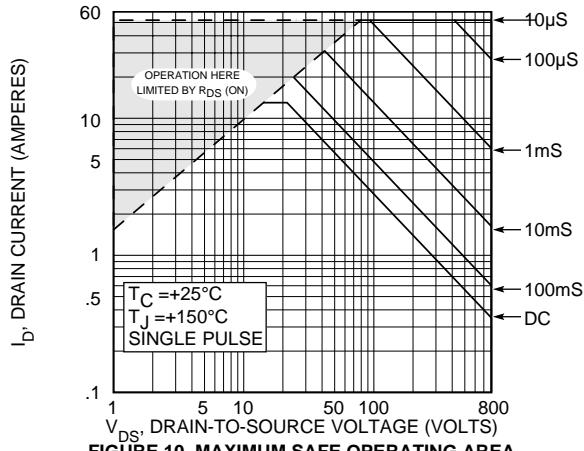


**FIGURE 8, ON-RESISTANCE vs. TEMPERATURE**

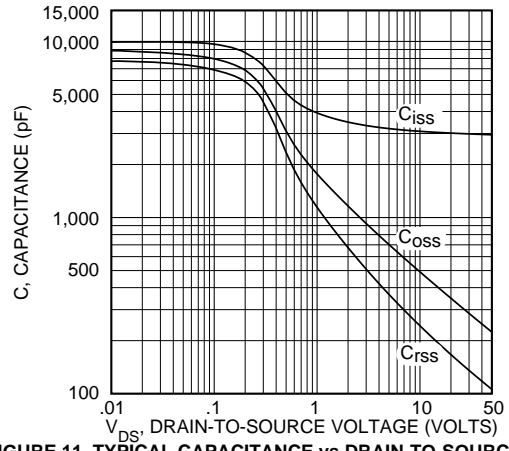


**FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE**

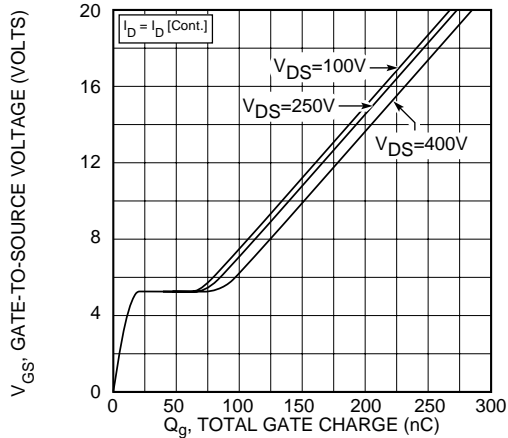
**APT8065BVFR**



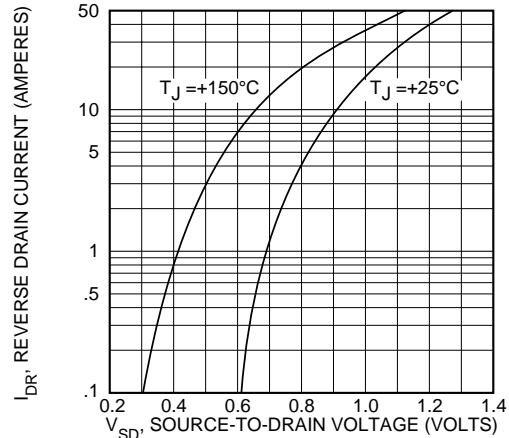
**FIGURE 10, MAXIMUM SAFE OPERATING AREA**



**FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE**

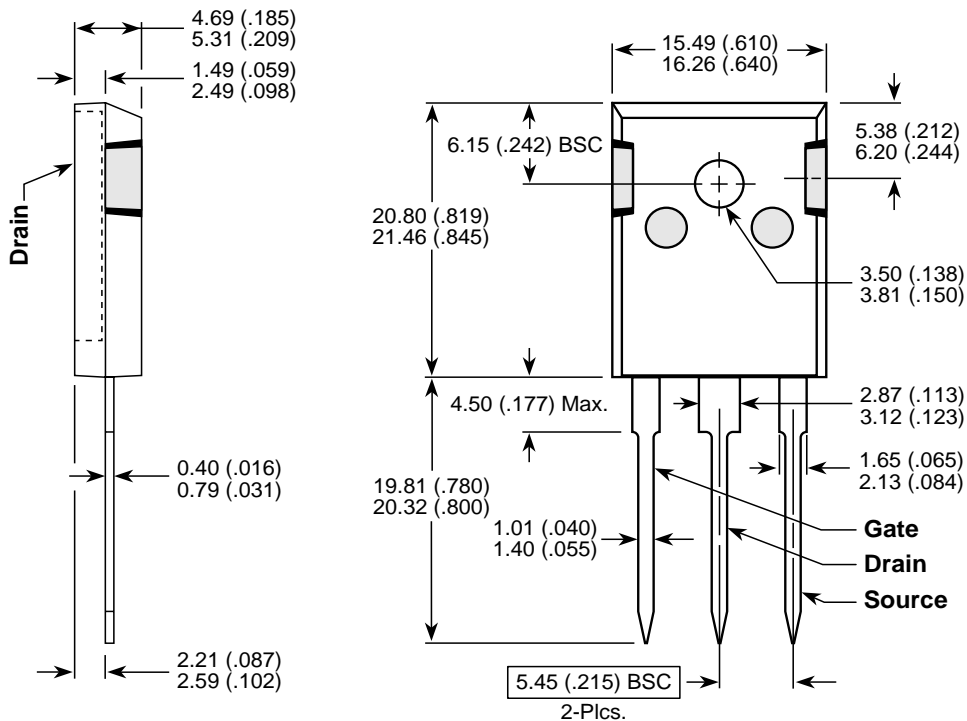


**FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE**



**FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE**

**TO-247 Package Outline**



Dimensions in Millimeters and (Inches)